

Active Bias Controller

Characteristics

- Supplies stable bias current even at low battery voltage and extreme ambient temperature variatior
- Low voltage drop of 0.7V

Application notes

- Stabilizing bias current of NPN transistors and FET's from less than 0.2mA up to more than 200mA
- Ideal supplement for Sieget and other transistors
- also usable as current source up to 5mA
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101



Туре	Marking	Pin Configuration				Package
BCR400W	W4s	1=GND/ E_{NPN}	2=Contr/ B _{NPN}	3V _S	4=Rext/ C _{NPN}	SOT343

(E_{NPN}, B_{NPN}, C_{NPN} are electrodes of a stabilized NPN transistor)

Maximum Ratings

Parameter	Symbol	Value	Unit
Source voltage	V _S	18	V
Control current	I _{Contr.}	10	mA
Control voltage	V _{Contr.}	16	V
Reverse voltage between all terminals	V _R	0.5	
Total power dissipation, $T_{\rm S}$ = 117 °C	P _{tot}	330	mW
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-65 150	
			•

Thermal Resistance

Junction - soldering point ²⁾	R _{thJS}	≤ 100	K/W

¹Pb-containing package may be available upon special request

²For calculation of R_{thJA} please refer to Application Note Thermal Resistance





BCR400W



Parameter	Symbol	Values		Unit	
		min.	typ.	max.	
DC Characteristics					
Additional current consumption	<i>I</i> ₀	-	20	40	μA
$V_{\rm S} = 3 \rm V$					
Lowest stabilizing current	l _{min}	-	0.1	-	mA
$V_{\rm S}$ = 3 V					
DC Characteristics with stabilized NPN-Transistors					
Lowest sufficient battery voltage	V _{Smin}	-	1.6	-	V
<i>I</i> _B (NPN) < 0.5mA					
Voltage drop (V _S - V _{CE})	V _{drop}	-	0.65	-	
<i>I</i> _C = 25 mA					
Change of I _C versus h _{FE}	$\Delta I_{\rm C}/I_{\rm C}$	-	0.08	-	$\Delta h_{\rm FE}$ /
$h_{FE} = 50$					h _{FE}
Change of $I_{\rm C}$ versus $V_{\rm S}$	$\Delta I_{\rm C}/I_{\rm C}$	-	0.15	-	$\Delta V_{\rm S}/V_{\rm S}$
$V_{\rm S}$ = 3 V					
Change of $I_{\rm C}$ versus $T_{\rm A}$	$\Delta I_{\rm C}/I_{\rm C}$	-	0.2	_	%/K

Electrical Characteristics at T_A =25°C, unless otherwise specified



Collector current $I_{\rm C} = f(h_{\rm FE})$

 $I_{\rm C}$ and $h_{\rm FE}$ refer to stabilized NPN Transistor Parameter $R_{\rm ext.}$ (Ω)



Collector Current $I_{\rm C} = f(V_{\rm S})$

of stabilized NPN Transistor Parameter $R_{ext.}$ (Ω)



Voltage drop $V_{drop} = f(I_C)$



Collector current $I_{\rm C} = f(R_{\rm ext.})$ of stabilized NPN Transistor





Collector current $T_A = f(I_C)$

of stabilized NPN Transistor Parameter: $R_{ext}(\Omega)$ 10 ³ mΑ 2.2 6 10² 26 2 65 10¹ 290 760 10 ⁰ 4.3k 10 °C -40 -20 0 20 40 60 80 100 120 160 T_A

Control current $I = f(R_{ext.})$

in current source application



Control current $I = f(T_A)$

in current source application



Control current $I = f(V_S)$ in current source application





Total power dissipation $P_{tot} = f(T_S)$



Note that up to T_S =115°C it is not possible to exceed P_{tot} respecting the maximum ratings of V_S and $I_{Contr.}$ The collector or drain current (respectively) of the stabilized RF transistor does not affect BCR 400 directly, as it provides just the base current.

Typical application for GaAs FET with active bias controller





RF transistor controlled by BCR400



Be aware that BCR400 stabilized bias current of transistors in an active control loop

In order to avoid loop ascillation (hunting), time constants must be chosen adequately, i.e. **C1 >= 10 x C2**

RX/TX antenna switch, compatible to control logic and working at wide battery voltage range





Low voltage reference



Precision timer with BCR400 providing constant charge current







Foot Print



Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel





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